

BRCS200P016MC

Rev.D Dec.-2025

/ Descriptions

SOT23-3 P MOS

G- CHANNEL MOSFET in a SOT23-3 Plastic Package.

/ Features

M_J 200mW (T_C = 25°C)

I_D 100mA (V_{GS} = 0V, V_{DS} = 10V, f_{sw} = 10kHz)

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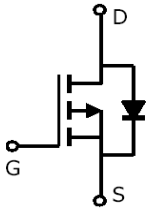
I_D 100mA (V_{GS} = 0V, V_{DS} = 10V, f_{sw} = 10kHz)

? F Grf [I Zk%

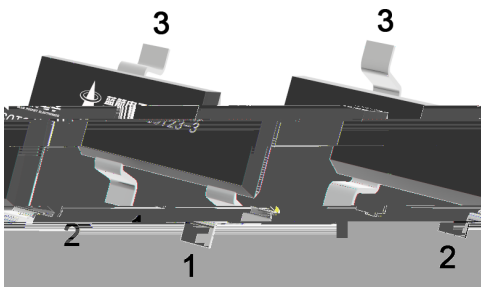
/ Applications

Power Management in Notebook computer, Portable Equipment and Battery powered systems.

/ Equivalent Circuit



/ Pinning



PIN1 G

PIN 2 S

PIN 3 D

/ Marking

Marking

C6H

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DSS}	-16	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current	I _D	-7.0	A
Pulsed Drain Current	I _{DM}	-30	A
Power Dissipation for Single Operation	P _D	1.2	W
Maximum Junction Temperature	T _j	150	
Storage Temperature Range	T _{stg}	-55 150	
Thermal Resistance-Junction to Ambient	R _{JA}	100	/W

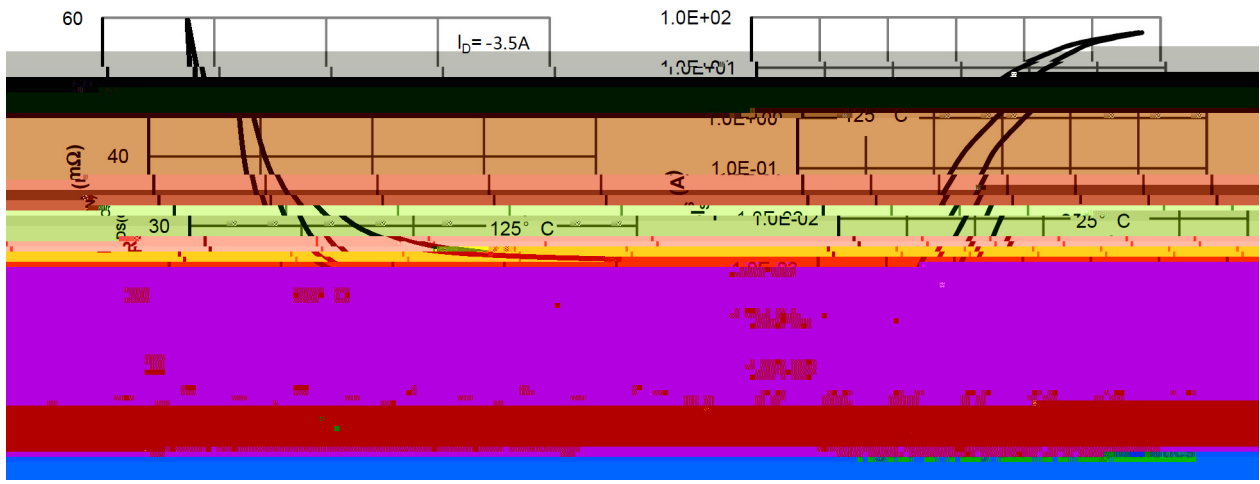
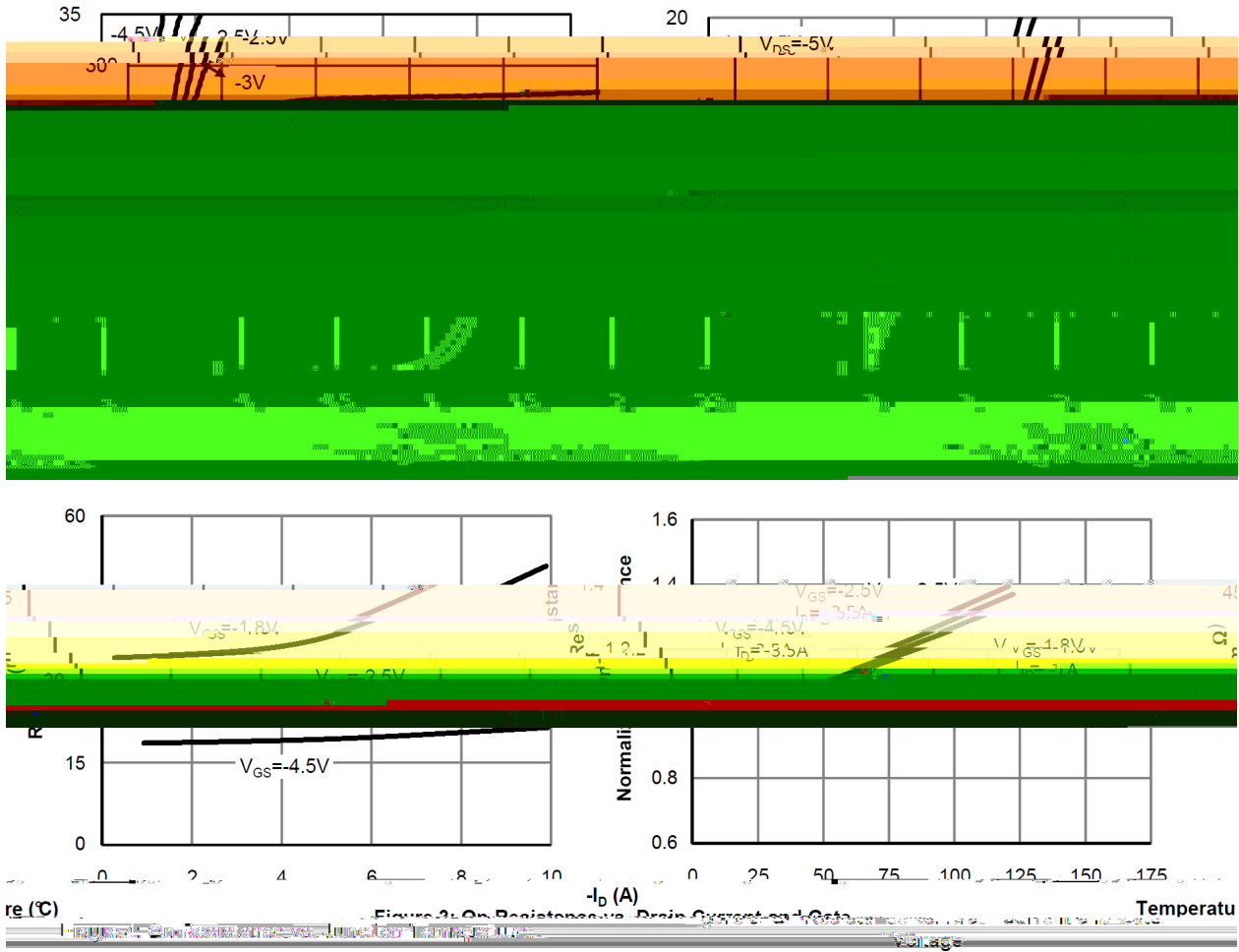
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =-250 A V _{GS} =0V	-16	-17		V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-12.8V V _{GS} =0V			-1.0	A
Gate-Body leakage current	I _{GSS}	V _{DS} =0V V _{GS} =±12V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =-250 A	-0.5	-0.6	-1.0	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-4.5V I _D =-3.5A		17.5	20	m
		V _{GS} =-2.5V I _D =-3.5A		26	30	
		V _{GS} =-1.8V I _D =-1A		40.5	100	
Diode Forward Voltage	V _{SD}	I _S =-1A V _{GS} =0V			-1.2	V
Gate resistance	R _g	V _{GS} =0V, f=1MHz V _{DS} =0V,		5.8		
Input Capacitance	C _{iss}	V _{GS} =0V V _{DS} =-5V f=1MHz		1350		pF
Output Capacitance	C _{oss}			290		
Reverse Transfer Capacitance	C _{rss}			250		

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	Q_g	$V_{GS}=-4.5V, \quad V_{DS}=-10V,$ $I_D=-7.0A$		13.2		nC
Gate Source Charge	Q_{gs}			1.5		
Gate Drain Charge	Q_{gd}			3.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=-4.5V \quad I_D=-7.0A$ $V_{DS}=-10V \quad R_{GEN}=3$		13.7		ns
Turn-On Rise Time	t_r			47.6		
Turn-Off Delay Time	$t_{d(off)}$			43.1		
Turn-Off Fall Time	t_f			29.5		

/ Electrical Characteristic Curve



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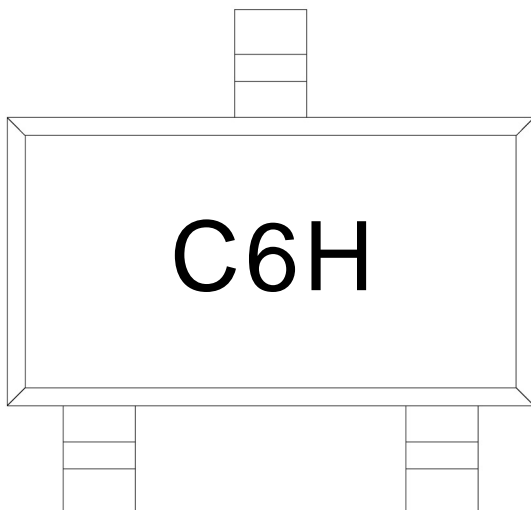


蓝箭电子
BLUE ROCKET ELECTRONICS

DATA SHEET

/ Electrical Characteristic Curve

/ Marking Instructions



C6

H

Note:

C6: Product Type Code

H: Company Code

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